

L Number	Hits	Search Text	DB	Time stamp
1	38	ueda near2 tetsuzo.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/22 14:17
-	24	iii near2 nitride and (both adj side) same deposit\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/31 10:20
-	78	iii near2 nitride and (top same bottom) same deposit\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/31 10:25
-	96	double near2 sid\$2 near2 (epitax\$4 or deposit\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/31 10:27
-	4	(double near2 sid\$2 near2 (epitax\$4 or deposit\$4)) and 117/\$4.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/31 10:37
-	0	5356831.pn. and remov\$3 near2 substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/31 10:40
-	2	5356831.pn. and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/12/31 10:40
-	353	olsen.in. and bow\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/09 18:08
-	2	olsen.in. and bow\$3 near10 wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/09 18:09
-	1280	bow\$3 near10 wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/09 18:09
-	38	bow\$3 near10 wafer same nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/10 11:05
-	96	bow\$3 near10 wafer near10 flat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/10 13:47
-	687	deposit\$ near15 wafer near10 flat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/10 13:50
-	70	deposit\$ near15 wafer near10 (flatten or flattening or flattens)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/10 13:50

	3	5562770.URPN.	USPAT	2004/02/10 13:53
	12	("3458369" "3808674" "3821033" "3997368" "4079506" "4159214" "4415373" "4631804" "4805071" "4830984" "5158907" "5319570").PN.	USPAT	2004/02/10 13:54
	225	direct near5 heat\$4 and 117/\$.ccls.	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/10 14:32
	66	direct near5 heat\$4 and 117/\$.ccls. and (chemical adj vapor adj deposition or cvd)	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/10 14:36
	1911	without near4 heat near2 sink	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/10 14:36
	77	(without near4 heat near2 sink) and (cvd or chemical adj vapor adj deposition)	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/10 14:38
	6	((without near4 heat near2 sink) and (cvd or chemical adj vapor adj deposition)) and 117/\$.ccls.	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/10 14:37
	5	(without near4 heat near2 sink) same (direct\$4 near2 heat\$4) and (cvd or chemical adj vapor adj deposition)	USPAT; US_PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/10 14:38